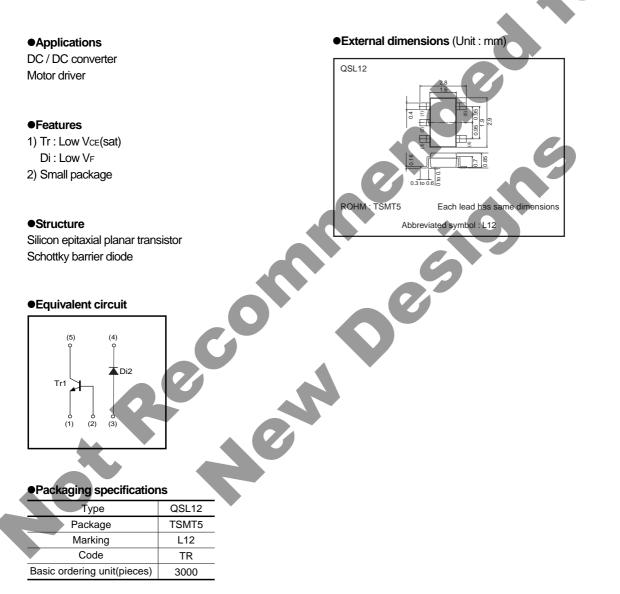
General purpose transistor (isolated transistor and diode) QSL12

A 2SD2675 and a RB461F are housed independently in a TSMT5 package.



Transistors

Absolute maximum ratings (Ta=25°C)

Tr1

Parameter	Symbol	Limits	Unit
Collector-base voltage	Vсво	30	V
Collector-emitter voltage	VCEO	30	V
Emitter-base voltage	Vebo	6	V
Collector current	lc	1	A
Collector current	Іср	2	A *1
Power dissipation	Pc	0.9	W/ELEMENT *2
Junction temperature	Tj	150	°C
Range of storage temperature	Tsta	-40 to +125	°C

Di2

Parameter	Symbol	Limits	Unit
Peak reverse voltage	Vrm	25	V
Reverse voltage (DC)	Vr	20	V
Average rectified forward current	lF	700	mA
Forward current surge peak (60Hz, 1∞)	IFSM	3	A
Power dissipation	PD	0.7	W/ELEMENT *
Junction temperature	Tj	125	°C
Range of storage temperature	Tstg	-40 to +125	O°

Tr1&Di2

Symbol	Limits	Unit
D-	0.5	W/TOTAL *1
PD	1.25	W/TOTAL *2
	Symbol P⊳	Pp 0.5

Electrical characteristics (Ta=25°C)

IFI										
Parameter	5	Symbol		imits		U	nit	_		
Collector-base voltage		Vсво		30		١	/			
Collector-emitter voltag	ge	Vceo		30		١	/			
Emitter-base voltage		Vebo		6		١	/			
Collector current		lc		1		A				
		Іср		2		ŀ		*1		
Power dissipation		Рс		0.9	\	N/ELE		*2		
Junction temperature		Tj		150		٥				
Range of storage temp	perature	Tstg	-40	to +12	25	°(2	_		
*1 Single pulse, Pw=1ms *2 Mounted on a 25mm×25mr Di2	n×¹0.8mm cera	amic subst	rate							
Parameter	-	Sym	bol	Lin	nits		Unit			
Peak reverse voltage		VR	м	2	5		V			
Reverse voltage (DC)		VF	२	2	0		V			
Average rectified forwa	ard current	lF		70	00		mA			
Forward current surge pe	ak (60Hz, 1	∞) IFS	м	3	3		А			
Power dissipation		P		0.		W/	ELEM	<u>ENT *</u>		
Junction temperature		Tj		12	-		°C			
Range of storage temp * Mounted on a 25mm×25mm		Tst	<u> </u>	-40 to	+125		°C			
Tr1&Di2 Parameter	Symbol	Limit	<u> </u>		Unit					
		0.5	5	\M/		AI *1				
Total power disipation	PD -	1.25	;		/TOT/					
*1 Each terminal mounted on a *2 Mounted on a 25mm×25mn •Electrical character Tr1	n×¹0.8mm cera	amic subst	rate.	5				0	9	
Parameter	r	Syn	nból	Min.	Typ.	Max.	Unit		Conditions	
Collector-base breakdo			_	30	-		V	Ic=10μA		
Collector-emitter break				30	-		V	lc=1mA		
Emitter-base breakdow		BV	EBO	6	-	-	V	Iε=10μA		
Collector cutoff current		Ici	во	_		100	nA	Vcb=30V		
Emitter cutoff current		IEI	во	-		100	nA	Veb=6V		
Collector-emitter satura	tion voltag	e Vc	(sat)		120	350	mV	Ic/Iв=500m	nA/25mA	
DC current gain		h	FE	270	-	680	-	Vce/Ic=2V	/100mA	*
Transition frequency		f	T		320	_	MHz	VCE=2V, IE	==−100mA, f=′	00MHz*
Collector output capacit	tance) Co	dc	-	7	-	pF	Vсв=10V,	IE=0A, f=1MH	<u> </u>
y Duland			÷ –							

Di2

» Pul

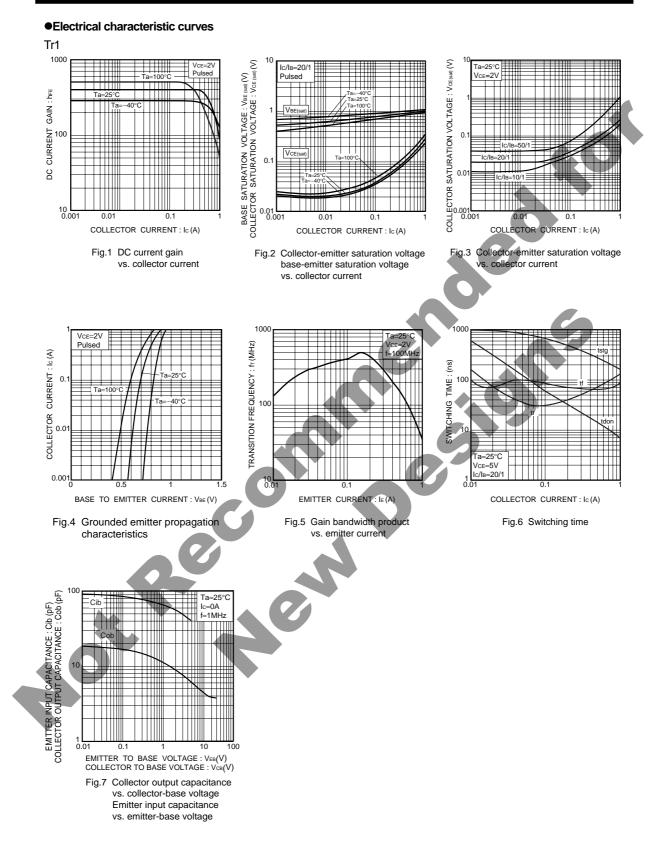
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	VF	-	450	490	mV	IF=700mA
Reverse current	IR	-	-	200	μA	VR=20V
Reverse recovery fime	trr	-	9	_	ns	IF=IR=100mA, Irr=0.1IR

QSL12

2/4

QSL12

Transistors



ROHM

Transistors





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